

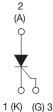
VS-25TTS..FPPbF Series, VS-25TTS..FP-M3 Series

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Thyristor High Voltage, Phase Control SCR, 25 A





TO-220AB FULL-PAK

PRODUCT SUMMARY					
Package	TO-220FP				
Diode variation	Single SCR				
I _{T(AV)}	16 A				
V _{DRM} /V _{RRM}	800 V, 1200 V				
V _{TM}	1.25 V				
I _{GT}	45 mA				
T_J	- 40 °C to 125 °C				

FEATURES

- · Designed and qualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- 125 °C max. operating junction temperature
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS				
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	Α			
I _{RMS}		25	^			
V _{RRM} /V _{DRM}		800/1200	V			
I _{TSM}		350	A			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T _J		- 40 to 125	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-25TTS08FPPbF, VS-25TTS08FP-M3	800	800	10			
VS-25TTS12FPPbF, VS-25TTS12FP-M3	1200	1200	10			



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
PANAMETEN	STWIBOL	TEST CONDITIONS	TYP. MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	$T_C = 51$ °C, 180° conduction half sine wave	16		
Maximum RMS on-state current	I _{RMS}		25	Α	
Maximum peak, one-cycle,	L	10 ms sine pulse, rated V _{RRM} applied	300	_ ^	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	350		
Maximum 12t for finding	l ² t	10 ms sine pulse, rated V _{RRM} applied	450	A ² s	
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied	630	A ² S	
Maximum I ² √t for fusing	I ² √t	t = 0.1ms to 10 ms, no voltage reapplied	6300	A²√s	
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C	1.25	V	
On-state slope resistance	r _t	T 105 °C	12.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C	1.0	V	
Maximum reverse and direct lockage current	1 /1	T _J = 25 °C	0.5		
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_{J} = 125 \text{ °C}$ $V_{R} = \text{Rated } V_{RRM} / V_{DRM}$	10		
Holding current	l _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, I_J = 25 °C		mA	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C 2			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		V/µs	
Maximum rate of rise of turned-on current	dl/dt		150	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	w	
Maximum average gate power	P _{G(AV)}		2.0	- VV	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	60		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA	
		Anode supply = 6 V, resistive load, T _J = 125 °C	20		
	V _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v	
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	\ \ \	
Maximum DC gate voltage not to trigger	V_{GD}	T. = 125 °C V Poted value	0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value		mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T 105 %C	4	μs
Typical turn-off time	t _q	T _J = 125 °C	110	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T_J , T_{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque ————	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf ⋅ in)
Marking device			Occasional TO COOME FULL DAY (CANO)	25TTS08	BFP
			Case style TO-220AB FULL-PAK (94/V0)	25TTS12FP	

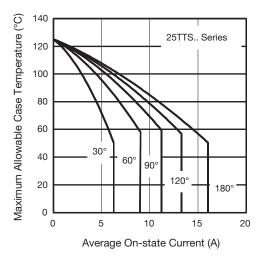


Fig. 1 - Current Rating Characteristics

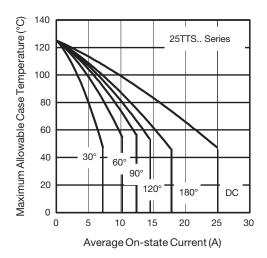


Fig. 2 - Current Rating Characteristics

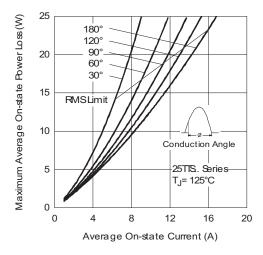


Fig. 3 - On-State Power Loss Characteristics

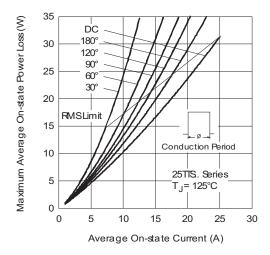


Fig. 4 - On-State Power Loss Characteristics

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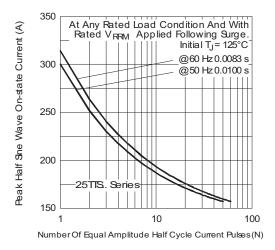


Fig. 5 - Maximum Non-Repetitive Surge Current

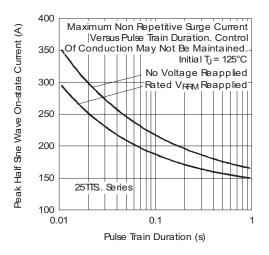


Fig. 6 - Maximum Non-Repetitive Surge Current

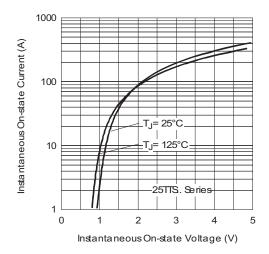


Fig. 7 - On-State Voltage Drop Characteristics

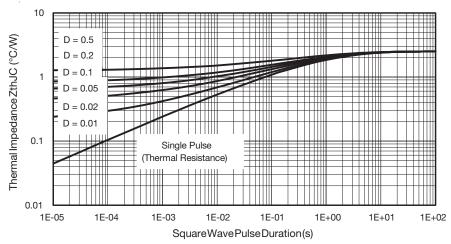


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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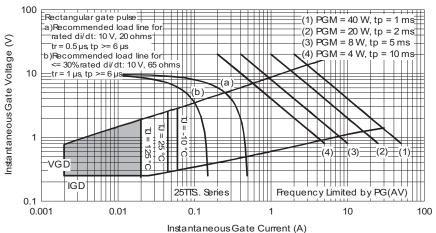
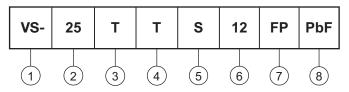


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- 3 Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

Standard recovery rectifier

7 - FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

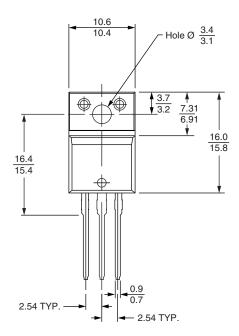
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08FPPbF	50	1000	Antistatic plastic tubes		
VS-25TTS08FP-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12FPPbF	50	1000	Antistatic plastic tubes		
VS-25TTS12FP-M3	50	1000	Antistatic plastic tubes		

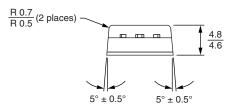
LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95072		
Dort marking information	TO-220FP PbF	www.vishay.com/doc?95069		
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456		

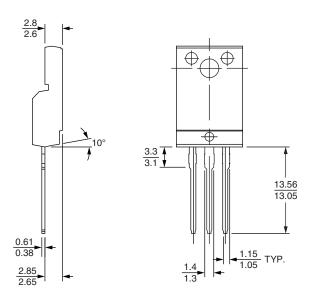


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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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